

# 18–23 GHz GaAs MMIC Power Amplifier



AA022P1-00

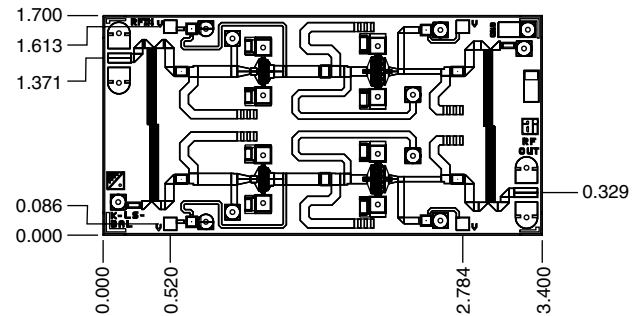
## Features

- Single Bias Supply Operation (6 V)
- 14 dB Typical Small Signal Gain
- 24.5 dBm Typical  $P_{1\text{ dB}}$  Output Power at 23 GHz
- 0.25  $\mu\text{m}$  Ti/Pd/Au Gates
- 100% On-Wafer RF and DC Testing
- 100% Visual Inspection to MIL-STD-883 MT 2010

## Description

Alpha's two-stage balanced K band GaAs MMIC power amplifier has a typical  $P_{1\text{ dB}}$  of 24.5 dBm with 13 dB associated gain and 11% power added efficiency at 23 GHz. The chip uses Alpha's proven 0.25  $\mu\text{m}$  MESFET technology, and is based upon MBE layers and electron beam lithography for the highest uniformity and repeatability. The FETs employ surface passivation to ensure a rugged reliable part with through-substrate via holes and gold-based backside metallization to facilitate a conductive epoxy die attach process. All chips are screened for small signal S-parameters and power characteristics prior to shipment for guaranteed performance. A broad range of applications exist in both the high reliability and commercial areas where high power and gain are required.

## Chip Outline



Dimensions indicated in mm.  
All DC (V) pads are 0.1 x 0.1 mm and RF In, Out pads are 0.07 mm wide.  
Chip thickness = 0.1 mm.

## Absolute Maximum Ratings

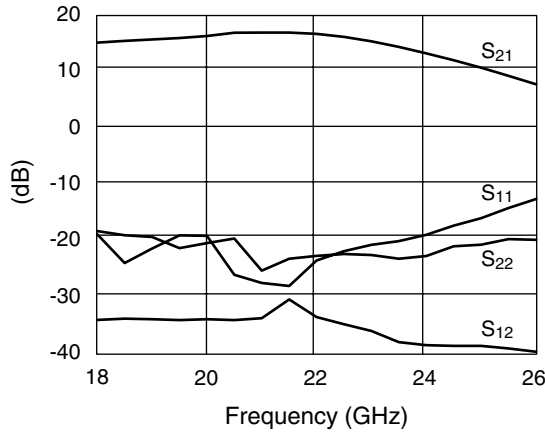
Characteristic	Value
Operating Temperature ( $T_C$ )	-55°C to +90°C
Storage Temperature ( $T_{ST}$ )	-65°C to +150°C
Bias Voltage ( $V_D$ )	7 $V_{DC}$
Power In ( $P_{IN}$ )	22 dBm
Junction Temperature ( $T_J$ )	175°C

## Electrical Specifications at 25°C ( $V_{DS} = 6\text{ V}$ )

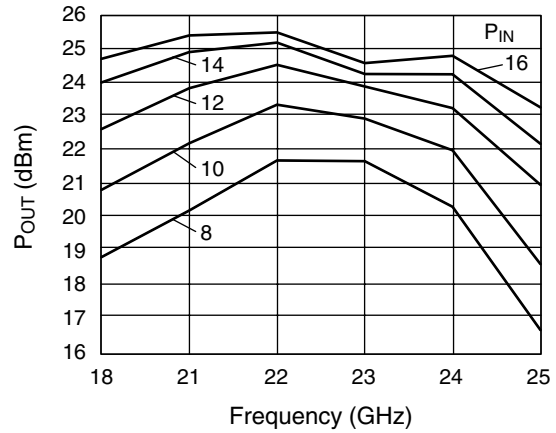
Parameter	Condition	Symbol	Min.	Typ. <sup>2</sup>	Max.	Unit
Drain Current (at Saturation)		$I_{DS}$		300	390	mA
Small Signal Gain	F = 18–23 GHz	G	12	14		dB
Input Return Loss	F = 18–23 GHz	$RL_I$		-15	-10	dB
Output Return Loss	F = 18–23 GHz	$RL_O$		-17	-10	dB
Output Power at 1 dB Gain Compression	F = 23 GHz	$P_{1\text{ dB}}$	22	24.5		dBm
Saturated Output Power	F = 23 GHz	$P_{SAT}$	24	25.5		dBm
Gain at Saturation	F = 23 GHz	$G_{SAT}$		13		dB
Thermal Resistance <sup>1</sup>		$\theta_{JC}$		39		°C/W

1. Calculated value based on measurement of discrete FET.  
2. Typical represents the median parameter value across the specified frequency range for the median chip.

### Typical Performance Data

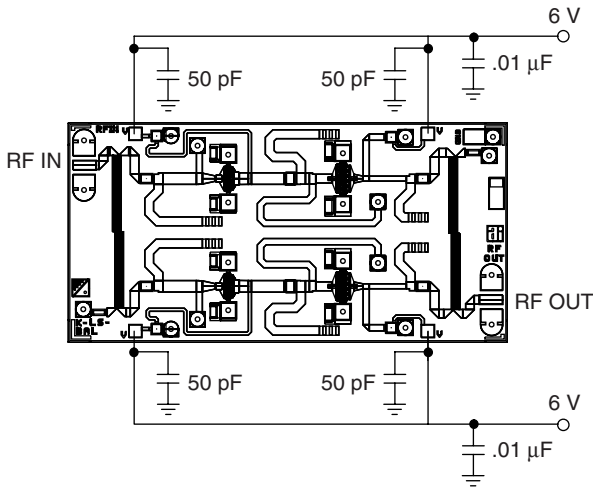


Typical Small Signal Performance S-Parameters (V<sub>DS</sub> = 6 V)



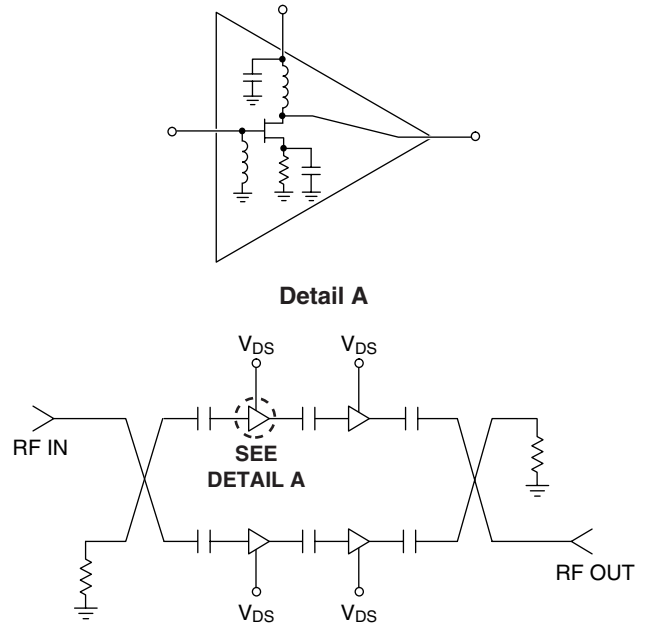
Output Characteristics as a Function of Frequency and Input Drive Level (V<sub>DS</sub> = 6 V)

### Bias Arrangement



For biasing on, adjust V<sub>DS</sub> from zero to the desired value (6 V recommended). For biasing off, reverse the biasing on procedure.

### Circuit Schematic



This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.